

**WEST****Freeform Search****Database:**

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**Term:**

"light emitting device" and semiconductor adj  
layers and p-type adj layer and n-type adj layer  
and ohmic and mirror and thickness

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<u>DB Name</u>	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u>
USPT,PGPB,JPAB,EPAB,DWPI,TDBD	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and reflector	15	<u>L11</u>
USPT,PGPB,JPAB,EPAB,DWPI,TDBD	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and reflector adj thickness	0	<u>L10</u>
USPT,PGPB,JPAB,EPAB,DWPI,TDBD	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and reflector adj thickness	0	<u>L9</u>
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USPT	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and mirror and micro adj meter	0	<u>L7</u>
USPT	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and mirror and micro meter	168410	<u>L6</u>
USPT	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and mirror and micron	1	<u>L5</u>
USPT	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and mirror and angstrom	6	<u>L4</u>
USPT	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and mirror adj4 thickness and angstrom	0	<u>L3</u>
USPT	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and mirror adj4 thickness	2	<u>L2</u>
USPT	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and mirror and thickness	20	<u>L1</u>